

MOTOROLA

SEMICONDUCTOR TECHNICAL DATA

Order this document
by 2N6282/D

Darlington Complementary Silicon Power Transistors

... designed for general-purpose amplifier and low-frequency switching applications.

- High DC Current Gain @ $I_C = 10 \text{ A dc}$ —
 $h_{FE} = 2400 \text{ (Typ)}$ — 2N6282, 2N6283, 2N6284
 $= 4000 \text{ (Typ)}$ — 2N6285, 2N6286, 2N6287
- Collector-Emitter Sustaining Voltage —
 $V_{CE(sus)} = 60 \text{ Vdc (Min)}$ — 2N6282, 2N6285
 $= 80 \text{ Vdc (Min)}$ — 2N6283, 2N6286
 $= 100 \text{ Vdc (Min)}$ — 2N6284, 2N6287
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors

*MAXIMUM RATINGS

Rating	Symbol	2N6282 2N6285	2N6283 2N6286	2N6284 2N6287	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector-Base Voltage	V_{CB}	60	80	100	Vdc
Emitter-Base Voltage	V_{EB}	5.0			Vdc
Collector Current — Continuous Peak	I_C	20 40			Adc
Base Current	I_B	0.5			Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	160 0.915			Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200			$^\circ\text{C}$

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.09	$^\circ\text{C/W}$

* Indicates JEDEC Registered Data.

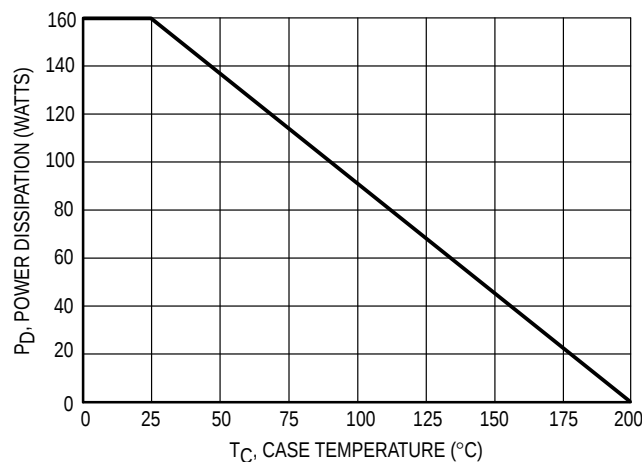


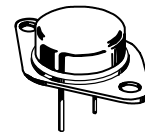
Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

NPN
2N6282
 thru
2N6284*
PNP
2N6285
 thru
2N6287*

*Motorola Preferred Device

DARLINGTON
20 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60, 80, 100 VOLTS
160 WATTS



CASE 1-07
TO-204AA
(TO-3)

2N6282 thru 2N6284 2N6285 thru 2N6287***ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 0.1 \text{ A dc}$, $I_B = 0$)	$V_{CE(sus)}$			Vdc
2N6282, 2N6285		60	—	
2N6283, 2N6286		80	—	
2N6284, 2N6287		100	—	
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	1.0	mAdc
2N6282, 2N6285		—	1.0	
2N6283, 2N6286		—	1.0	
2N6284, 2N6287		—	1.0	
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	—	0.5	mAdc
		—	5.0	
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	2.0	mAdc

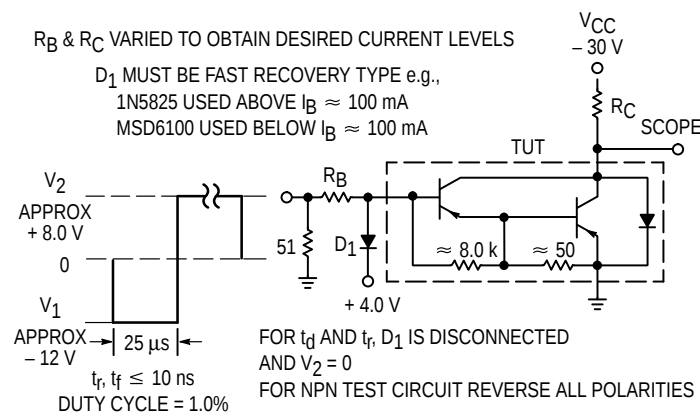
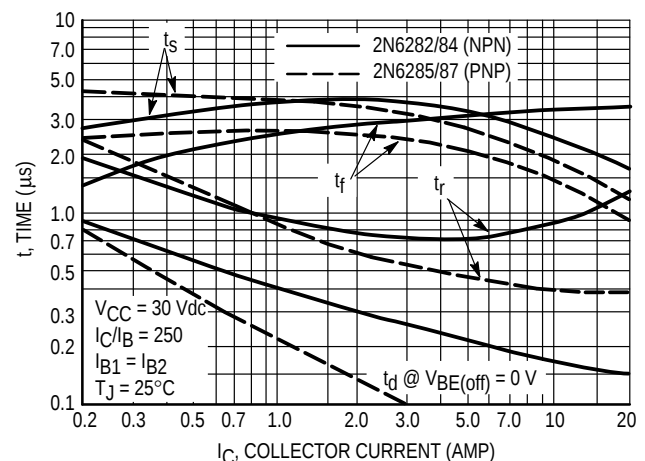
ON CHARACTERISTICS (1)

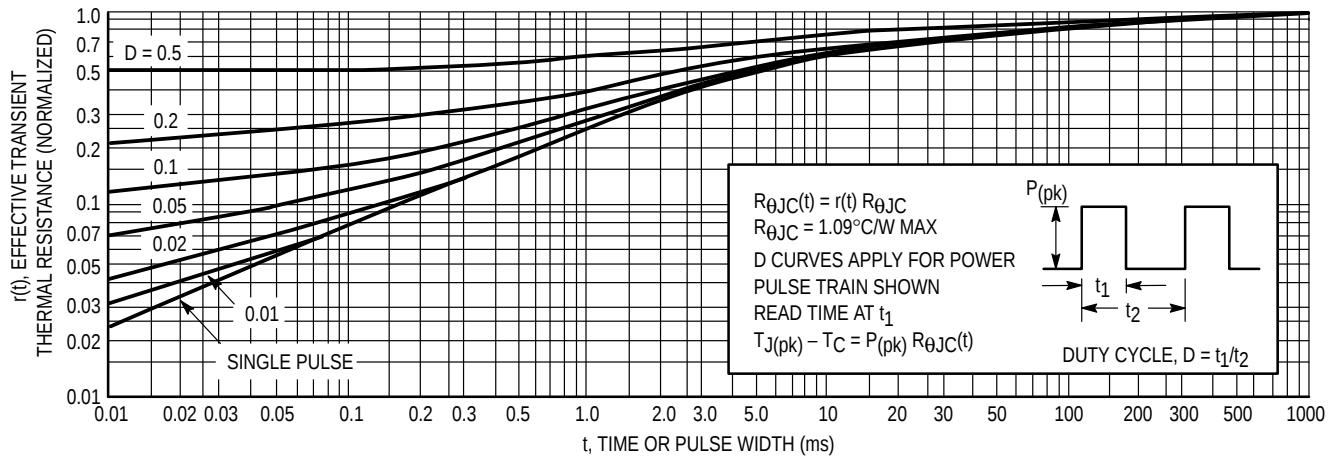
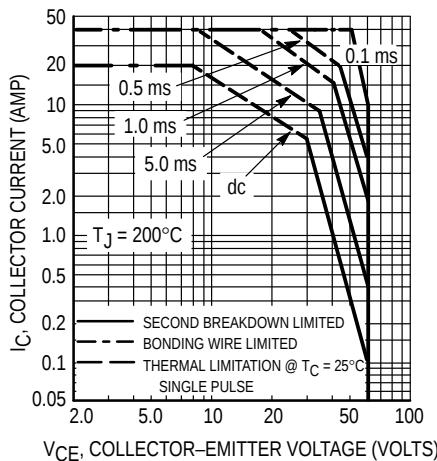
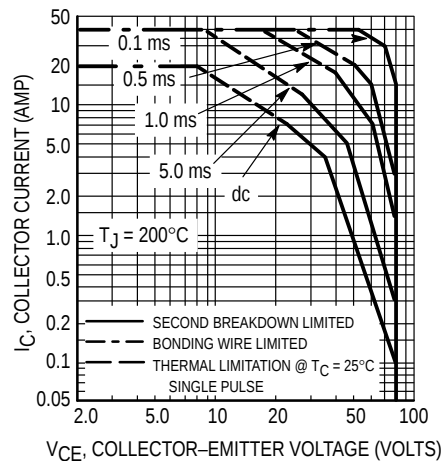
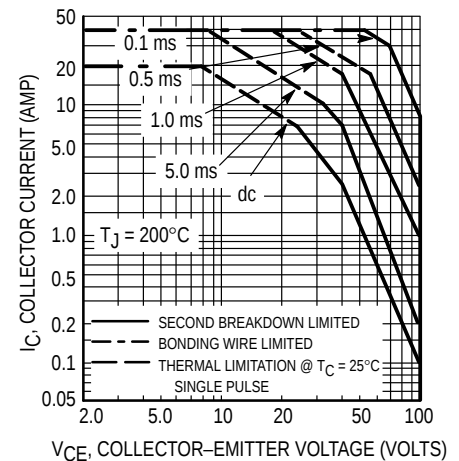
DC Current Gain ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 20 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$)	h_{FE}	750 100	18,000 —	—
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ A dc}$, $I_B = 40 \text{ mAdc}$) ($I_C = 20 \text{ A dc}$, $I_B = 200 \text{ mAdc}$)	$V_{CE(sat)}$	— —	2.0 3.0	Vdc
Base–Emitter On Voltage ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$)	$V_{BE(on)}$	—	2.8	Vdc
Base–Emitter Saturation Voltage ($I_C = 20 \text{ A dc}$, $I_B = 200 \text{ mAdc}$)	$V_{BE(sat)}$	—	4.0	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small–Signal Short–Circuit Forward Current Transfer Ratio ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	$ h_{fe} $	4.0	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)	C_{ob}	— —	400 600	pF
Small–Signal Current Gain ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	300	—	—

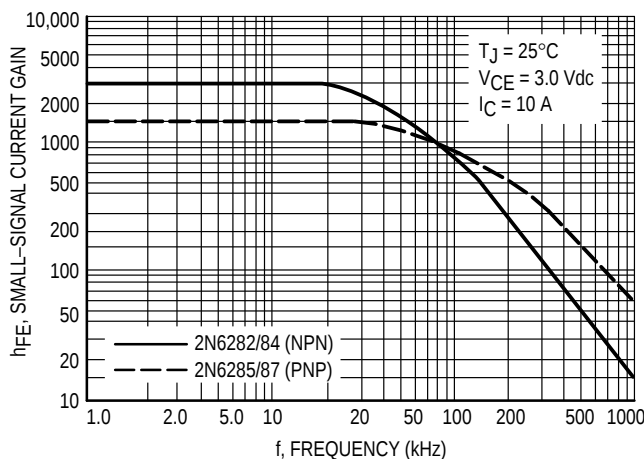
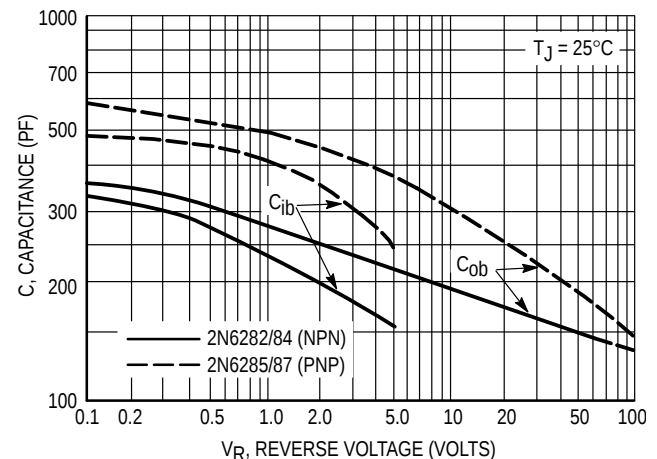
* Indicates JEDEC Registered Data.

(1) Pulse test: Pulse Width = 300 μs , Duty Cycle = 2%**Figure 2. Switching Times Test Circuit****Figure 3. Switching Times**

2N6282 thru 2N6284 2N6285 thru 2N6287**Figure 4. Thermal Response****ACTIVE-REGION SAFE OPERATING AREA****Figure 5. 2N6282, 2N6285****Figure 6. 2N6283, 2N6286****Figure 7. 2N6284, 2N6287**

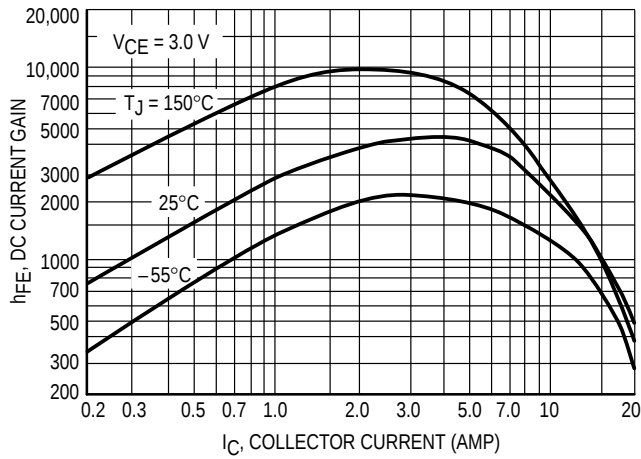
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e. the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5, 6 and 7 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 200^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

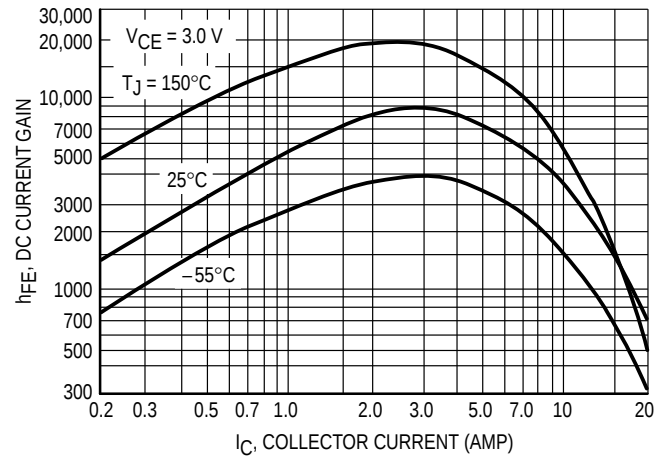
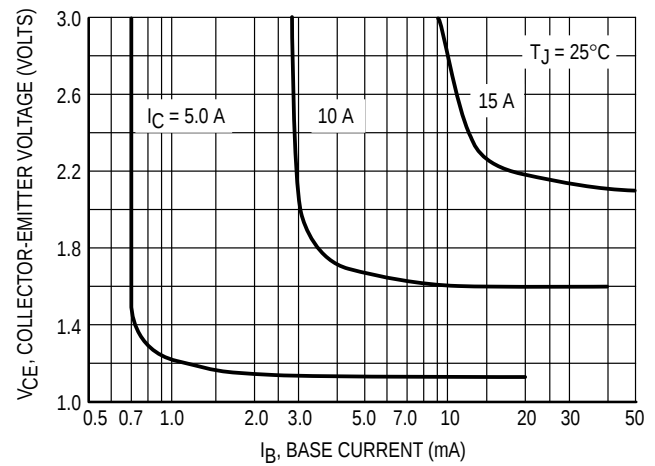
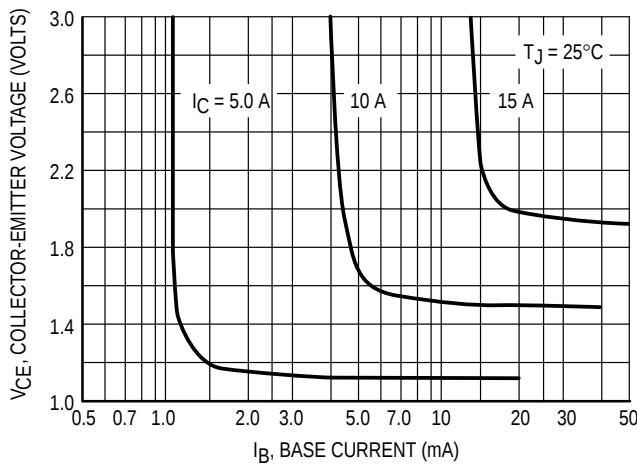
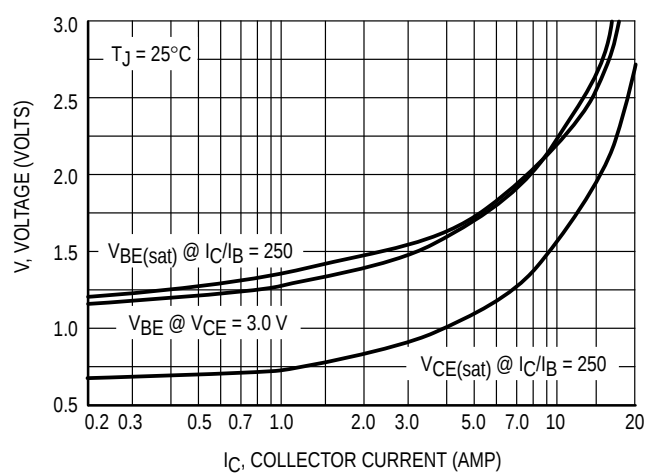
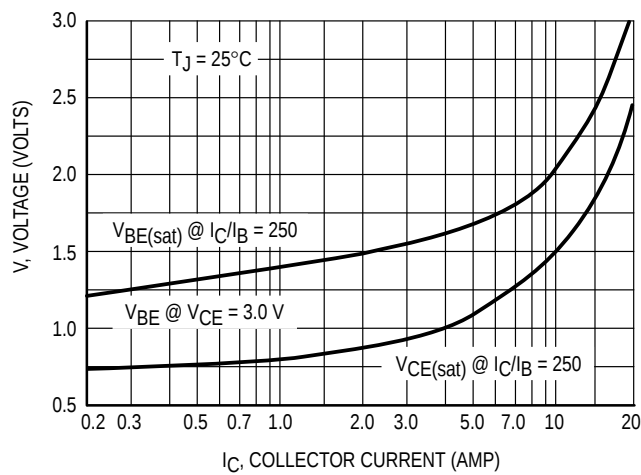
**Figure 8. Small-Signal Current Gain****Figure 9. Capacitance**

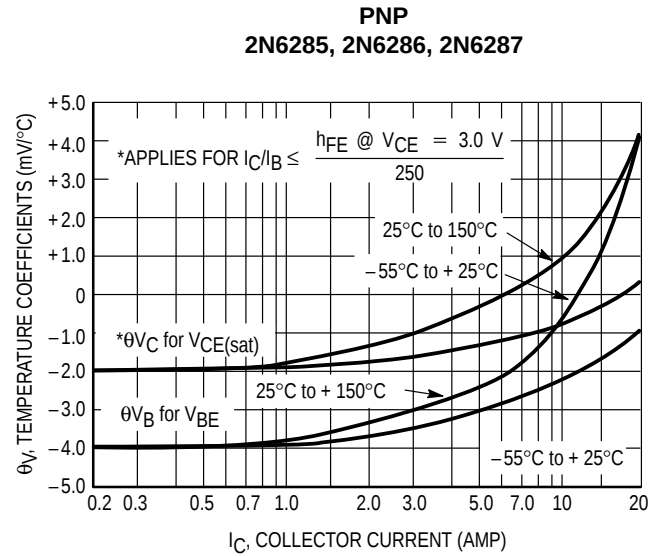
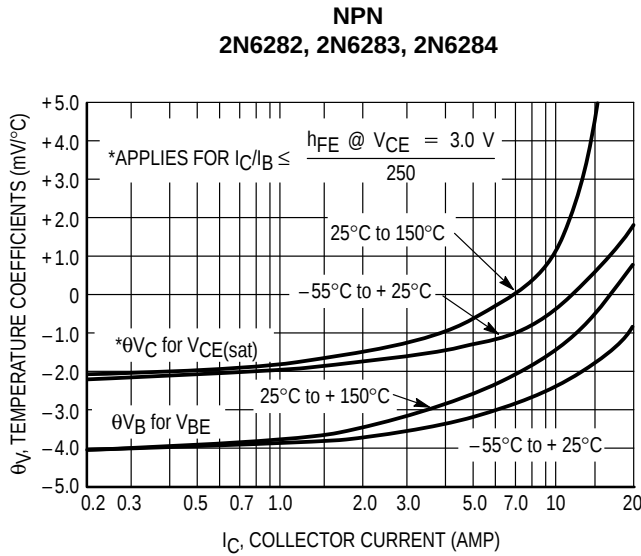
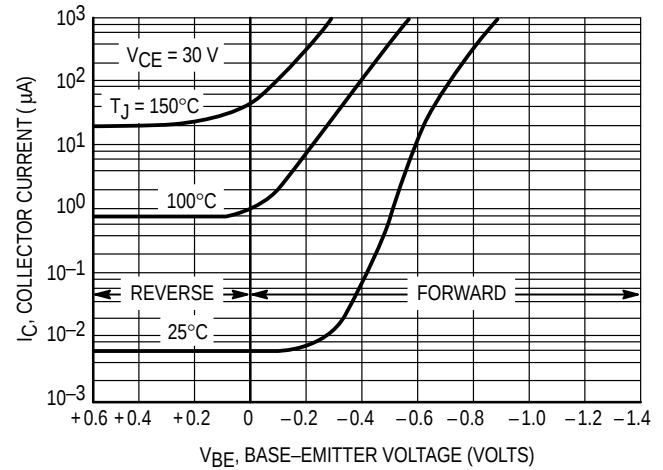
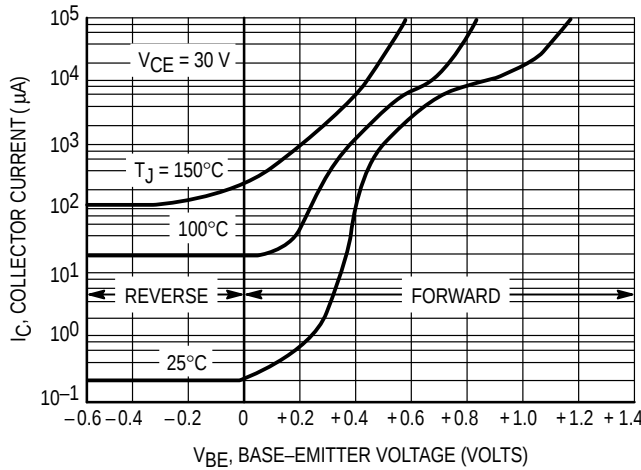
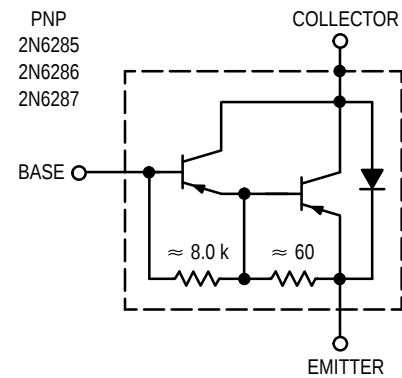
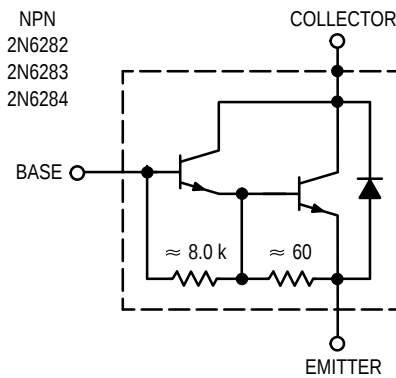
2N6282 thru 2N6284 2N6285 thru 2N6287

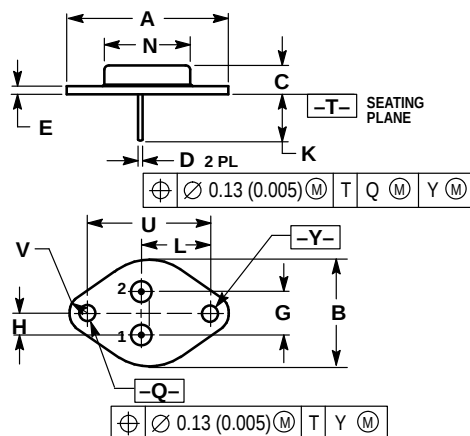
NPN
2N6282, 2N6283, 2N6284



PNP
2N6285, 2N6286, 2N6287

**Figure 10. DC Current Gain****Figure 11. Collector Saturation Region****Figure 12. "On" Voltages**

2N6282 thru 2N6284 2N6285 thru 2N6287**Figure 13. Temperature Coefficients****Figure 14. Collector Cut-Off Region****Figure 15. Darlington Schematic**

2N6282 thru 2N6284 2N6285 thru 2N6287**PACKAGE DIMENSIONS****NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	—	1.050	—	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	—	0.830	—	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:

- PIN 1: BASE
2: EMITTER
CASE: COLLECTOR

CASE 1-07
TO-204AA (TO-3)
ISSUE Z

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